

FR101-G Thru. FR107-G

Voltage: 50 to 1000 V

Current: 1.0 A

RoHS Device

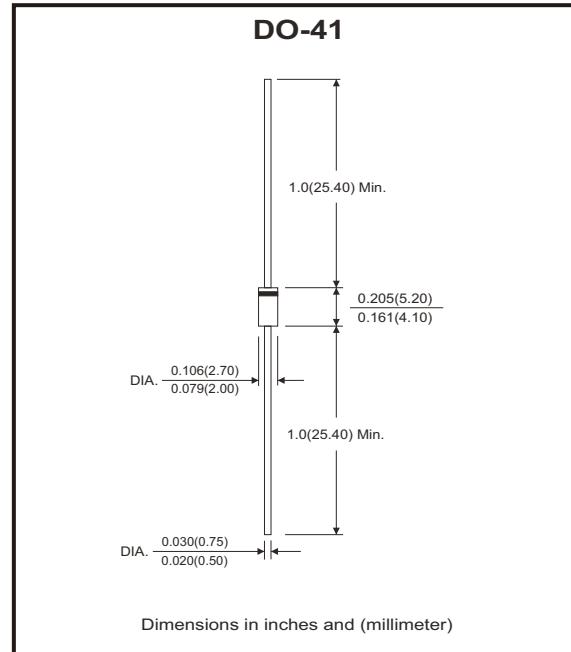


Features

- Fast switching for high efficiency.
- Diffused junction.
- Low reverse leakage current.
- Low forward voltage drop
- High current capability.

Mechanical data

- Case: JEDEC DO-41 molded plastic
- Epoxy: UL 94V-0 rate flame retardant
- Polarity: Color band denotes cathode
- Lead: Plated axial lead, solderable per MIL-STD-750, method 2026.
- Mounting position: Any



Circuit Diagram



Maximum Ratings (at TA=25°C unless otherwise noted)

Single phase, half wave, 60Hz, resistive or inductive load.
For capacitive load derate current by 20%.

Parameter	Symbol	FR101-G	FR102-G	FR103-G	FR104-G	FR105-G	FR106-G	FR107-G	Unit
Maximum repetitive peak reverse voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum average forward rectified current @TA=75°C	I _(AV)					1.0			A
Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	I _{FSM}					30			A
Maximum reverse recovery time (Note 1)	t _{rr}			150		250	500		nS
Operating temperature range	T _J				-55 ~ +150				°C
Storage temperature range	T _{STG}				-55 ~ +150				°C

Notes: 1. Measured with I_F=0.5A, I_R=1A, I_{RR}=0.25A.

Fast Recovery Rectifiers

Comchip
SMD Diode Specialist

Electrical Characteristics (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 1.0\text{A DC}$	V_F			1.3	V
DC reverse current at rated DC blocking voltage	$T_J = 25^\circ\text{C}$	I_R			5.0	μA
	$T_J = 100^\circ\text{C}$				100	
Junction capacitance	$V_R = 4\text{V}, f = 1.0\text{MHz}$	C_J		25		pF
		C_J		15		pF
Thermal resistance	Junction to ambient	$R_{\theta JA}$		25		$^\circ\text{C/W}$

RATING AND CHARACTERISTIC CURVES (FR101-G Thru. FR107-G)

Fig.1 - Forward Current Derating Curve

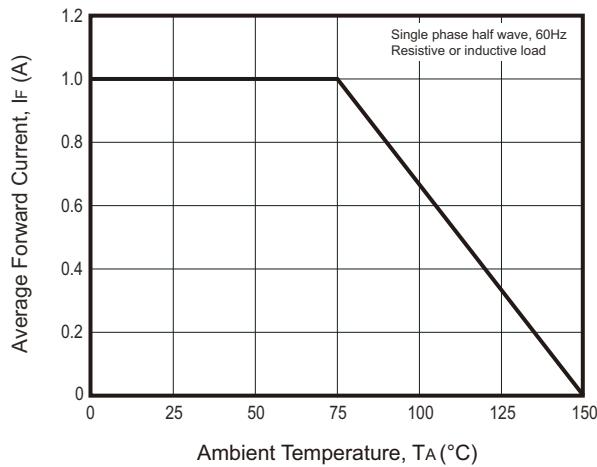


Fig.2 - Maximum Non-repetitive Surge Current

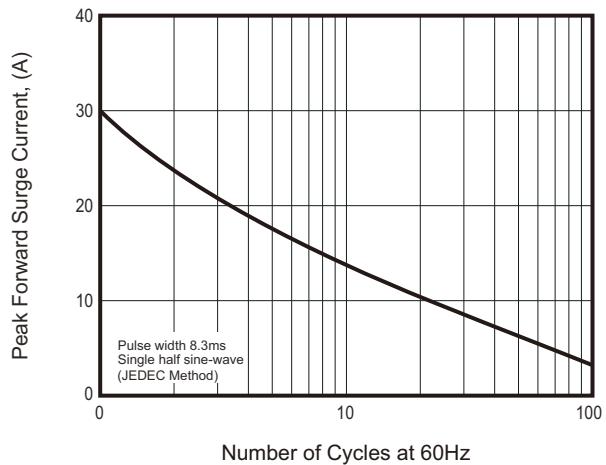


Fig.3 - Typical Junction Capacitance

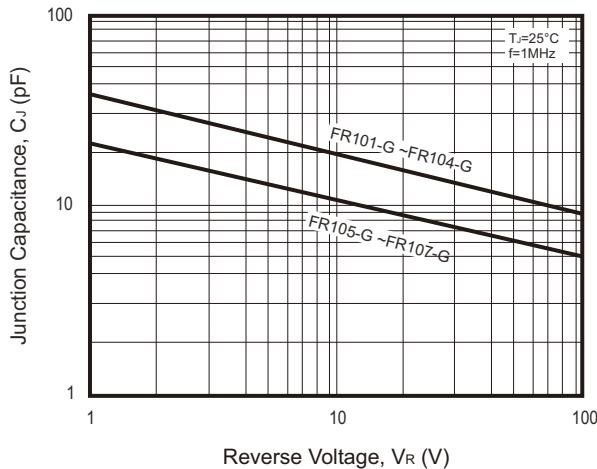
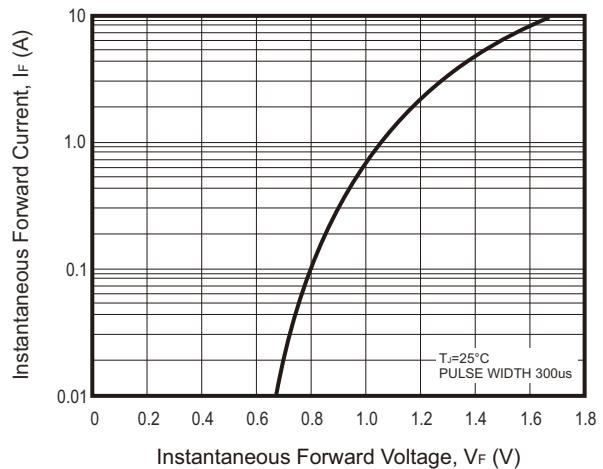


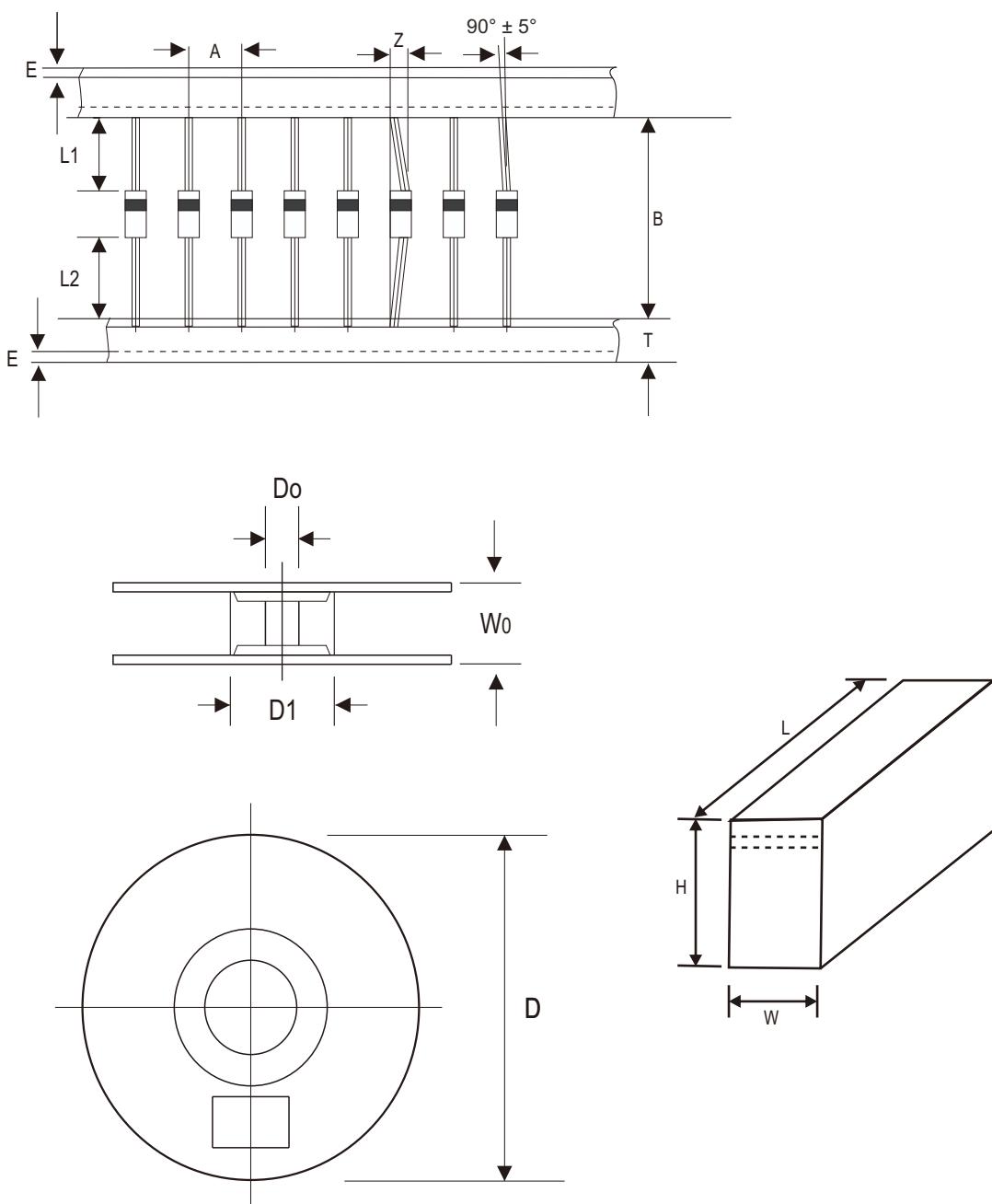
Fig.4 - Typical Forward Characteristics



Company reserves the right to improve product design , functions and reliability without notice.

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Taping Specification For Axial Lead Diodes



DO-41	SYMBOL	A	B	Z	T	E	L1-L2
	(mm)	5.00 ± 0.50	52.40 ± 1.50 - 0.40	1.20 (max)	6.00 ± 0.40	0.80 (max)	1.00 (max)
	(inch)	0.197 ± 0.020	2.063 ± 0.059 - 0.016	0.047 (max)	0.236 ± 0.016	0.031 (max)	0.039 (max)

DO-41	SYMBOL	D1	D0	D	W0	L	W	H
	(mm)	85.70 ± 0.30	16.60 ± 0.40	330.00	79.00 ± 1.00	255.00 ± 5.00	75.00 ± 5.00	150.00 ± 5.00
	(inch)	3.374 ± 0.012	0.654 ± 0.016	12.992	3.110 ± 0.039	10.039 ± 0.197	2.953 ± 0.197	5.906 ± 0.197

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